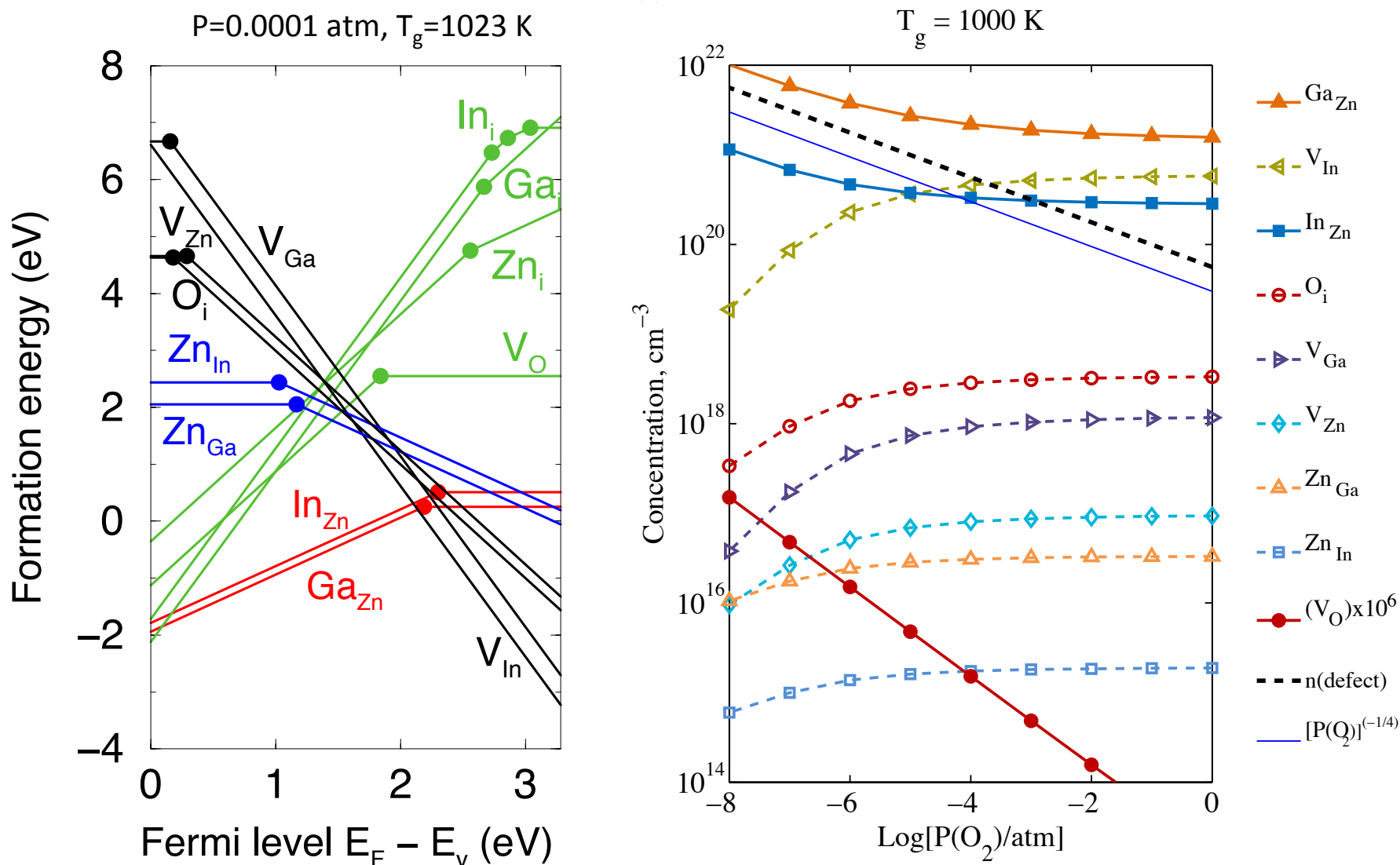


Defect formation/equilibrium carrier concentration: InGaZnO_4



Murat, Adler, Mason, Medvedeva, JACS (2013)

Oxygen vacancies, long believed to be the carrier source in this oxide, are scarce!
 Antisite defect is major electron donor; cation vacancy is major electron "killer"